

**SEMICONDUCTOR MEMORY DEVICE AND METHOD FOR PRODUCING THE SAME**

**Patent number:** KR9700227  
**Publication date:** 1997-01-06  
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**Classification:**  
- **international:** H01L27/108  
- **european:**  
**Application number:** KR19930016701 19930826  
**Priority number(s):** KR19930016701 19930826

**Abstract of KR9700227**

a transistor gate electrode(25) formed by being buried on an insulator(23) on a semiconductor substrate; a trench(101) formed on the semiconductor substrate through the insulator(23); and a semiconductor layer comprising impurity-doping regions(27,31A,31B) formed on top of the insulator (23) buried in the transistor gate electrode(25) and on the inner region of the trench(101).

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